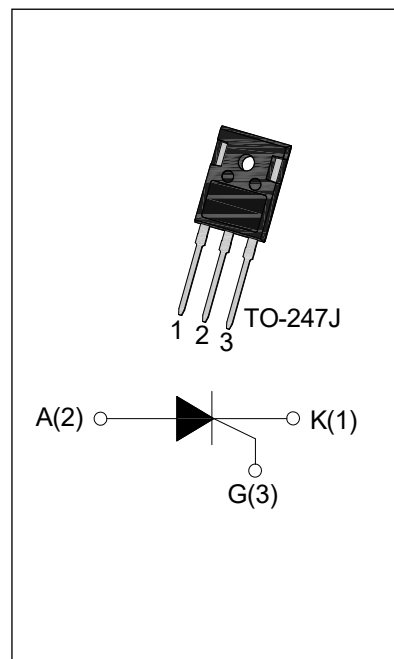




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1275SJ SCRs provide high dv/dt rate with high frequency noise immunity. Products are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc,UPS. Package TO-247J is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
V_{DRM} / V_{RRM}	1200	V
$I_{T(RMS)}$	75	A
I_{GT}	10~80	mA

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40~150	°C
Operating junction temperature range		T_j	-40~150	°C
Operating temperature range		T_{op}	-40~125	°C
Repetitive peak off-state voltage($T_j=25^{\circ}C$)		V_{DRM}	1200	V
Repetitive peak reverse voltage($T_j=25^{\circ}C$)		V_{RRM}	1200	V
Average on-state current		$I_{T(AV)}$	50	A
RMS on-state current	TO-247J ($T_C=105^{\circ}C$)	$I_{T(RMS)}$	75	A
Non repetitive surge peak on-state current ($t_p=10ms$)		I_{TSM}	800	A
I^2t value for fusing ($t_p=10ms$)		I^2t	3200	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	200	$A/\mu s$
Peak gate current		I_{GM}	10	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		P_{GM}	20	W

Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	1.3	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	10	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=150^{\circ}\text{C } R_L=3.3\text{K}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	150	mA
I_H	$I_T=1\text{A}$	-	-	120	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=150^{\circ}\text{C}$	1500	-	-	V/ μs
t_{on}	$I_G=80\text{mA } I_A=400\text{mA } I_R=40\text{mA}$ $T_j=25^{\circ}\text{C}$	-	5	-	μs
t_{off}		-	150	-	μs

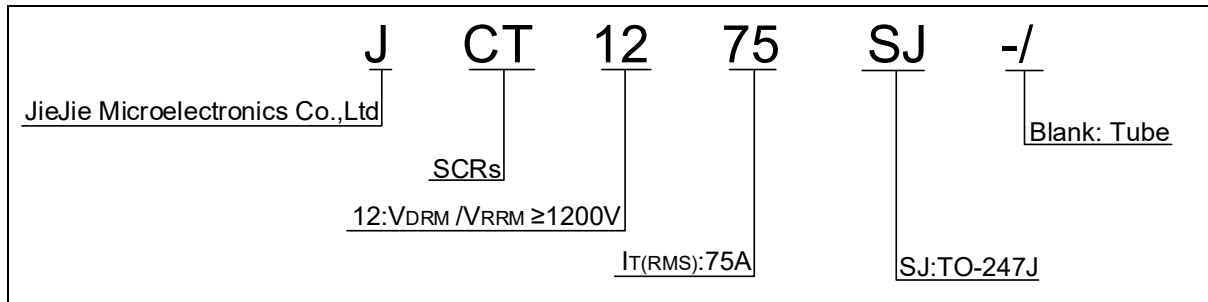
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=100\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^{\circ}\text{C}$	0.89	V
R_d	Dynamic resistance	$T_j=150^{\circ}\text{C}$	4.2	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	10	μA
I_{RRM}		$T_j=150^{\circ}\text{C}$	5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-247J	0.5	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

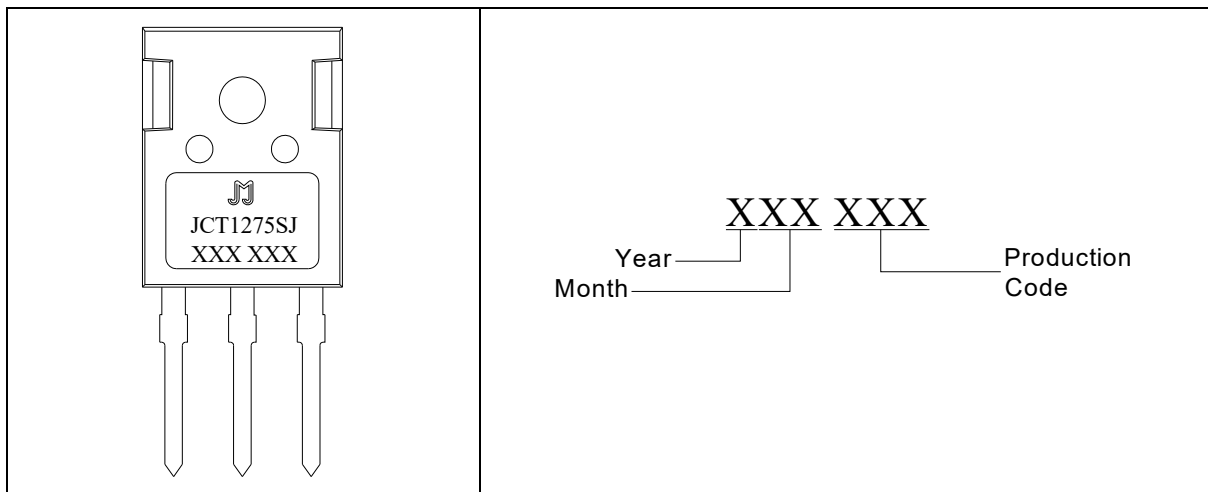


FIG.1: Maximum power dissipation versus RMS on-state current

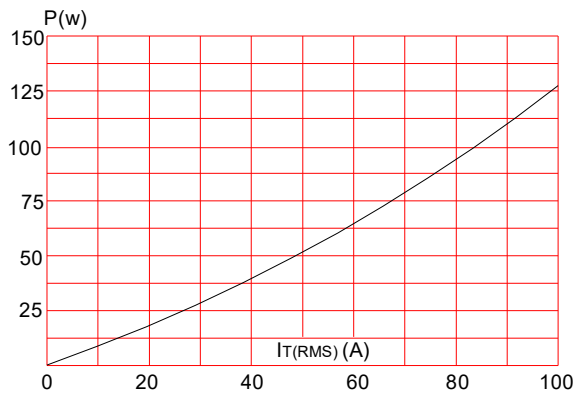


FIG.2: RMS on-state current versus case temperature

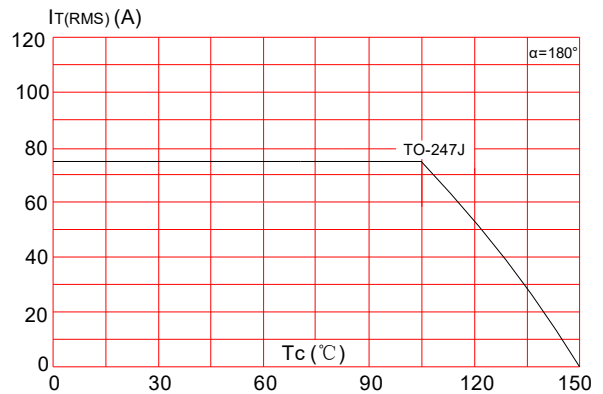


FIG.3: Surge peak on-state current versus number of cycles

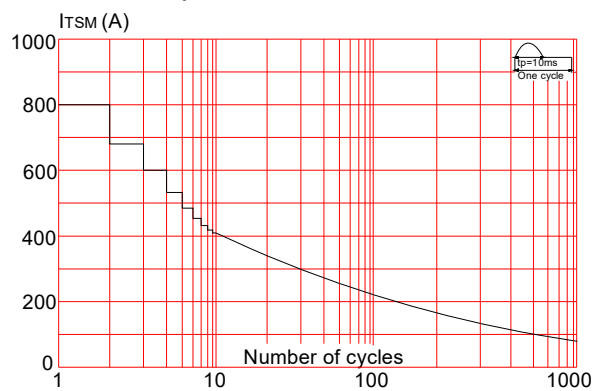


FIG.4: On-state characteristics (maximum values)

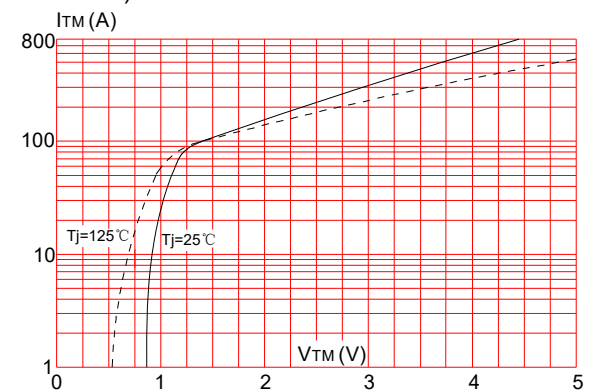


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $f \cdot t$ ($di/dt < 200\text{A}/\mu\text{s}$)

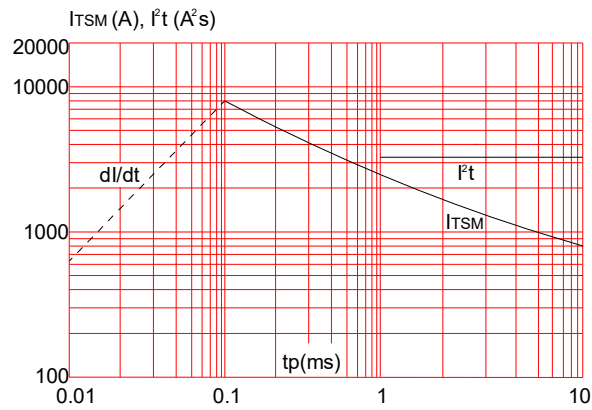


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

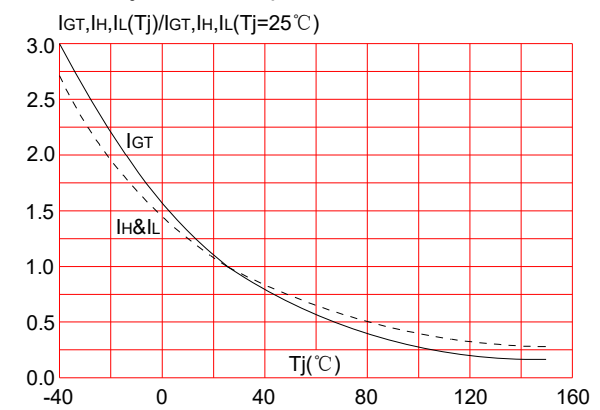
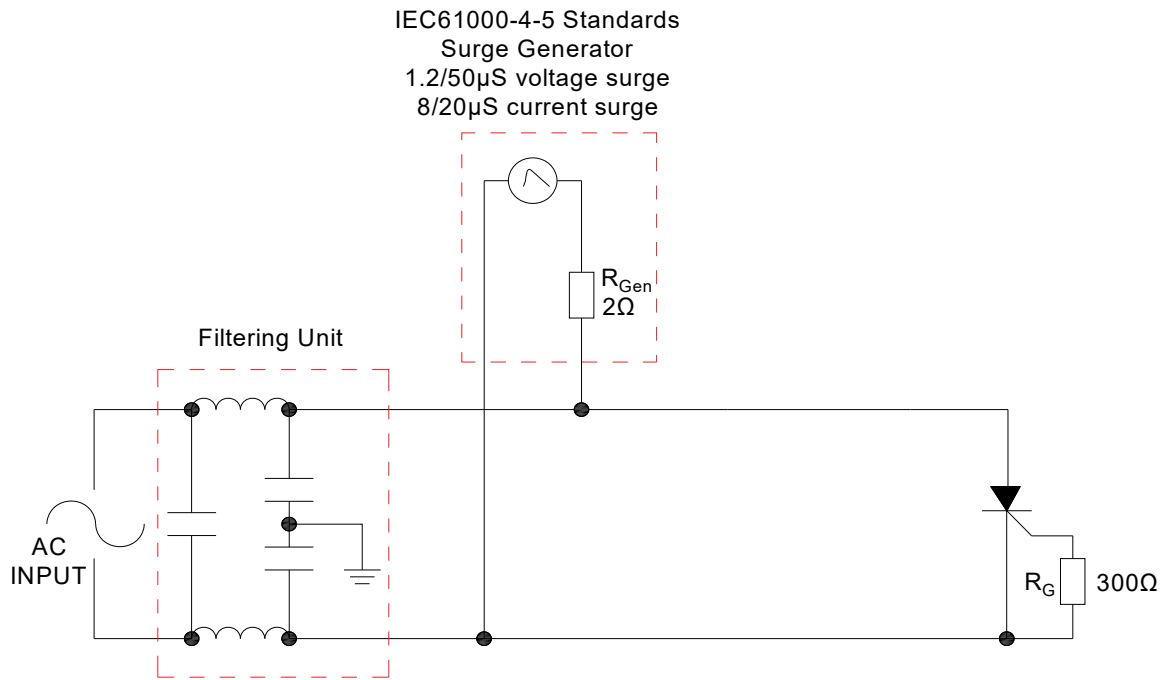


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



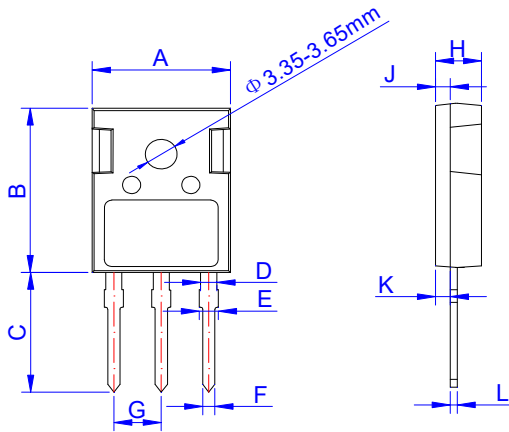
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1275SJ	1200	10~80	TO-247J	30	Tube

Document Revision History

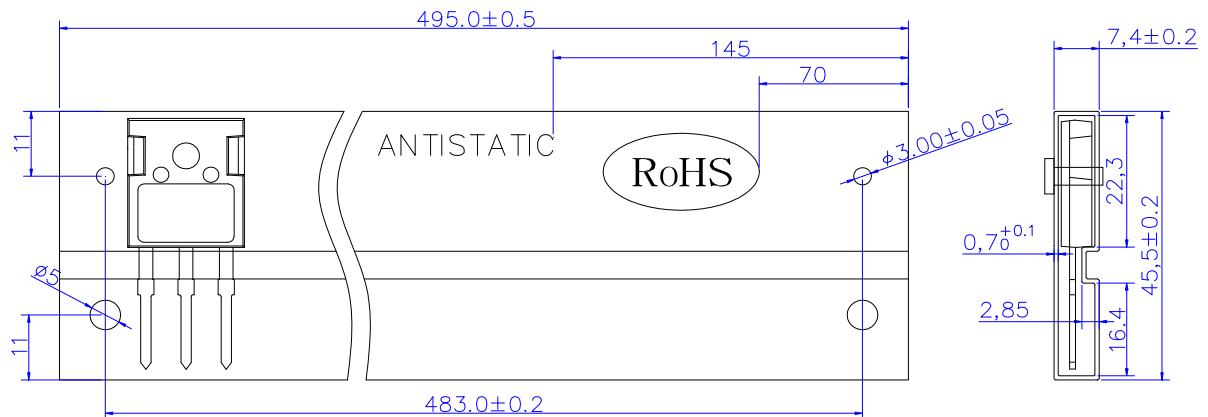
Date	Revision	Changes
Mar 19, 2022	1	Last update
May 26, 2022	2.1	Add V_{pp} & t_{on} & t_{off} & V_{TO} & R_d

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	22.20	0.819	0.827	0.835
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	5.25		5.65	0.207		0.222
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-247J	TUBE	30	450	2,250



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